

**AMENDMENTS TO THE SPECIFICATION**

Please amend the Abstract as follows:

A chalcogenide material is formed to a first thickness over the first conductive electrode material. The chalcogenide material includes  $A_xB_y$ . A metal layer that includes a metal is formed to a second thickness over the chalcogenide material. The metal including layer defines some metal including layer transition thickness for the first thickness of the chalcogenide material such that when said transition thickness is met or exceeded, said metal including layer when diffused within said chalcogenide material transforms said chalcogenide material from an amorphous state to a crystalline state. The second thickness being less than but not within 10% of said transition thickness. The metal including layer is irradiated effective to break a chalcogenide bond of the chalcogenide material and diffuse at least some of the metal into the chalcogenide material.